

Features

- Advanced Trench MOS Technology
- Fast Switching Speed
- Green Device Available
- Super Low Gate Charge

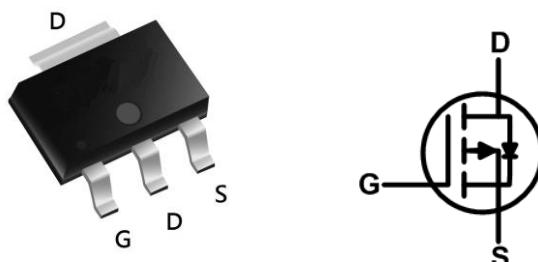
Product Summary

BVDSS	RDS(ON)	ID
-60V	130mΩ	-4.3A

Applications

- Motor Control.
- DC-DC Converters.
- Power Management Functions

SOT223 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	-4.3	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	-3.5	A
I _{DM}	Pulsed Drain Current ²	-14	A
P _D @T _A =25°C	Total Power Dissipation ³	2	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	62.5	°C/W
R _{θJA}	Thermal Resistance Junction-Ambient ¹ t≤10sec	---	32	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	10	°C/W

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=-250\mu\text{A}$	-60	---	---	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=-10\text{V}$, $I_D=-2\text{A}$	---	110	130	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}$, $I_D=-1.5\text{A}$	---	140	190	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=-250\mu\text{A}$	-1.0	---	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=-48\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{\text{DS}}=-48\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=150^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{\text{DS}}=-5\text{V}$, $I_D=-2\text{A}$	---	5.8	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{\text{DS}}=-20\text{V}$, $V_{\text{GS}}=-4.5\text{V}$, $I_D=-2\text{A}$	---	5.9	---	nC
Q_{gs}	Gate-Source Charge		---	2.9	---	
Q_{gd}	Gate-Drain Charge		---	1.8	---	
$T_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}}=-12\text{V}$, $V_{\text{GS}}=-10\text{V}$, $R_G=3.3\Omega$, $I_D=-1$	---	10	---	ns
T_r	Rise Time		---	17	---	
$T_{\text{d(off)}}$	Turn-Off Delay Time		---	22	---	
T_f	Fall Time		---	21	---	
C_{iss}	Input Capacitance	$V_{\text{DS}}=-15\text{V}$, $V_{\text{GS}}=0\text{V}$, $F=1\text{MHz}$	---	715	---	pF
C_{oss}	Output Capacitance		---	51	---	
C_{rss}	Reverse Transfer Capacitance		---	34	---	

Diode Characteristics

I_s	Continuous Source Current ^{1,5}	$V_{\text{G}}=V_{\text{D}}=0\text{V}$, Force Current	---	---	-4	A
V_{SD}	Diode Forward Voltage ²	$V_{\text{GS}}=0\text{V}$, $I_s=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_s , in real applications , should be limited by total power dissipation.

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P-Channel Typical Characteristics

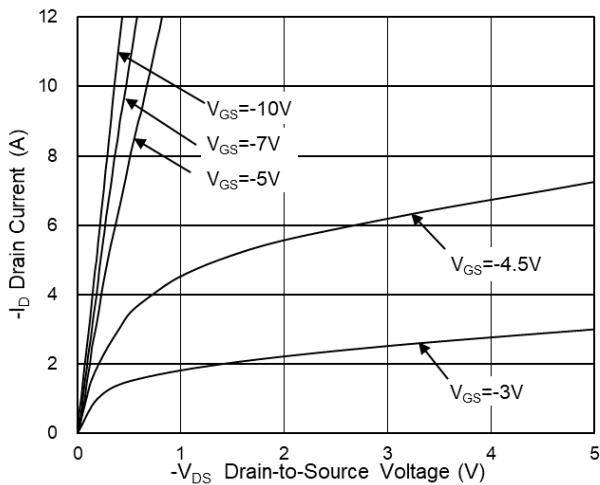


Fig.1 Typical Output Characteristics

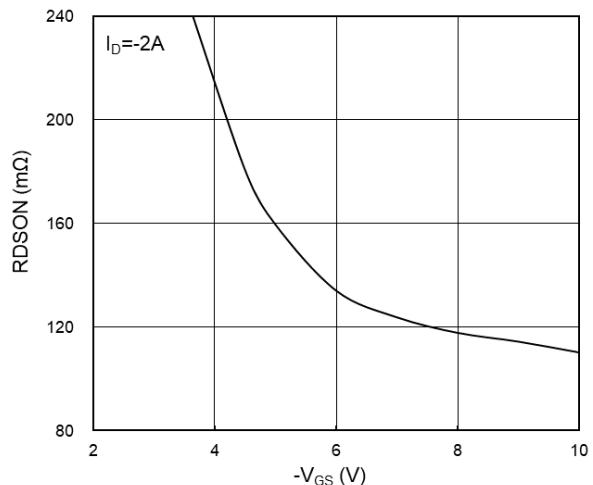


Fig.2 On-Resistance vs G-S Voltage

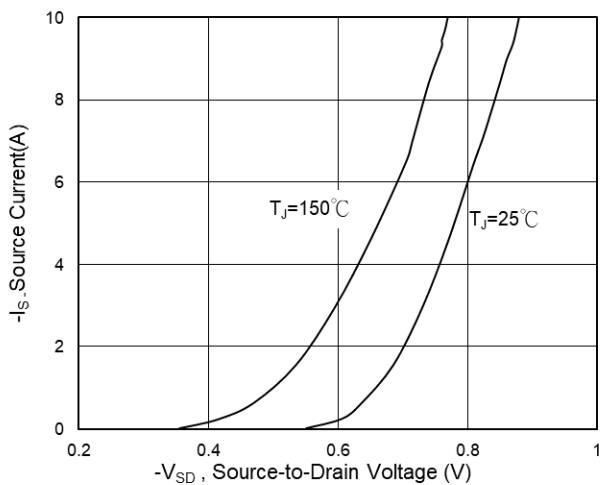


Fig.3 Source Drain Forward Characteristics

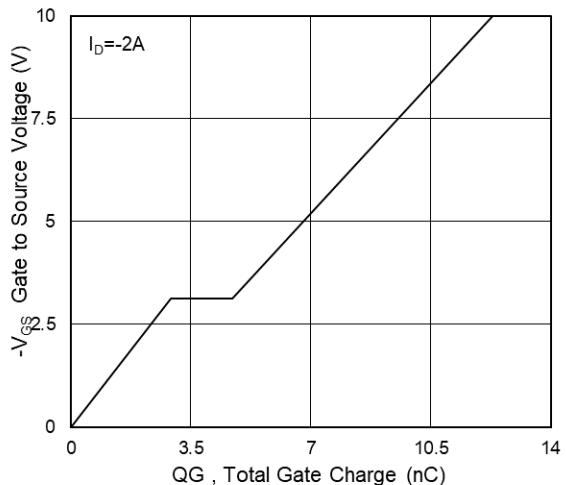


Fig.4 Gate-Charge Characteristics

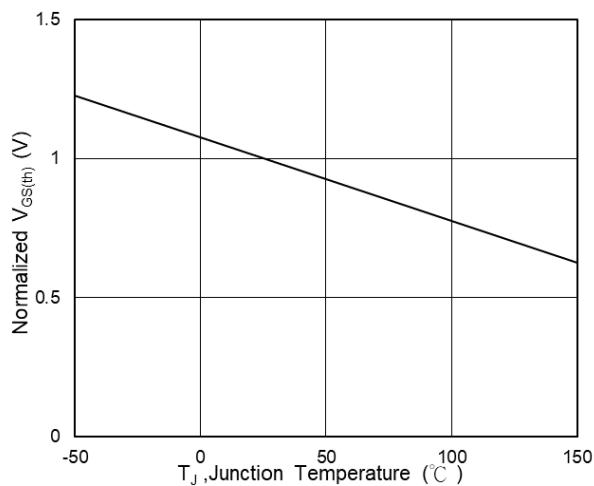


Fig.5 Normalized $V_{GS(th)}$ vs T_J

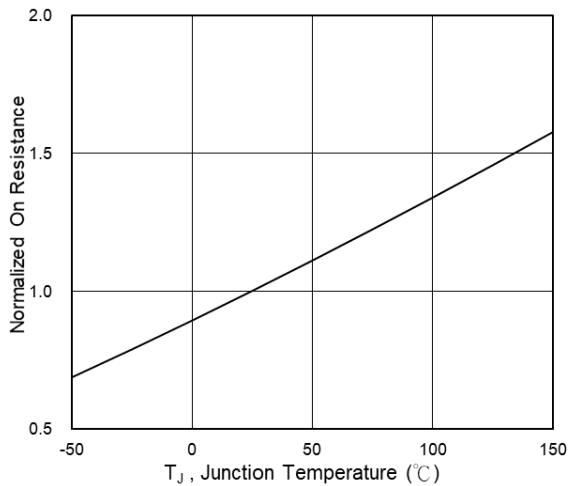


Fig.6 Normalized $R_{DS(on)}$ vs T_J

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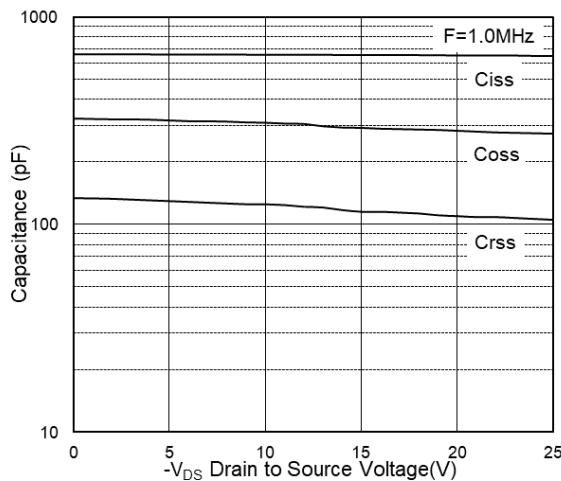


Fig.7 Capacitance

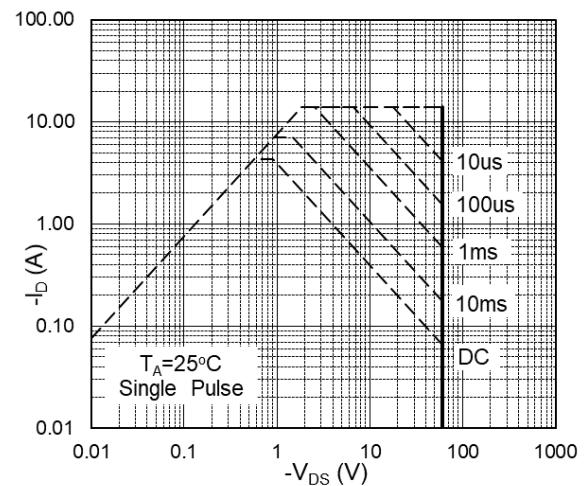


Fig.8 Safe Operating Area

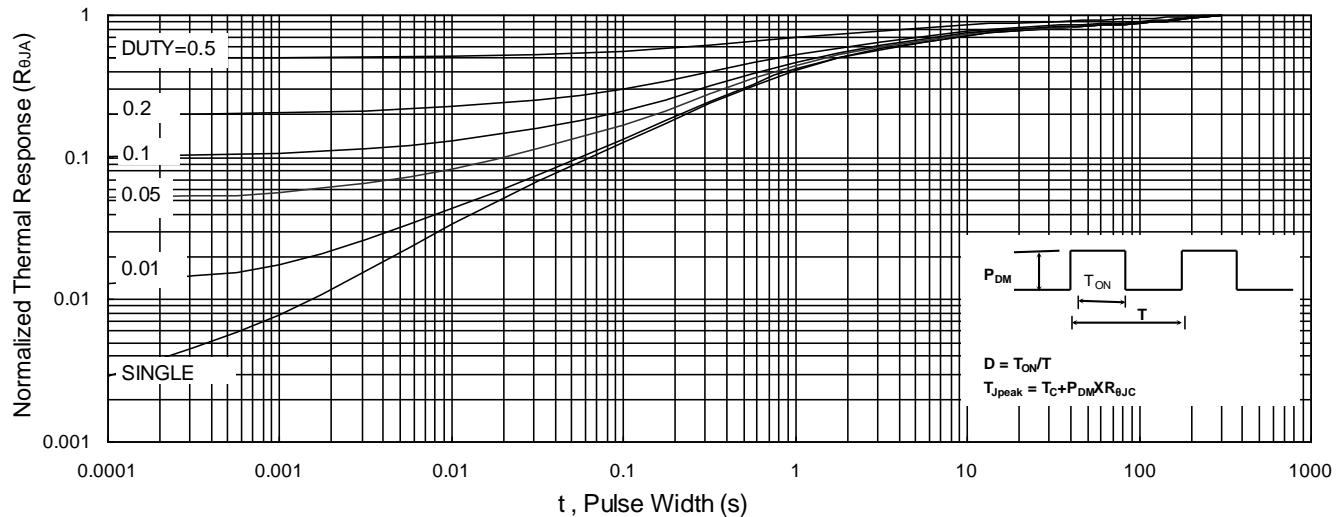


Fig.9 Normalized Maximum Transient Thermal Impedance

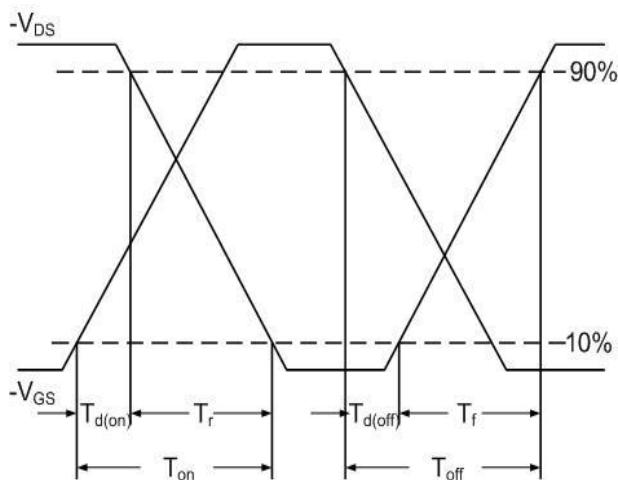


Fig.10 Switching Time Waveform

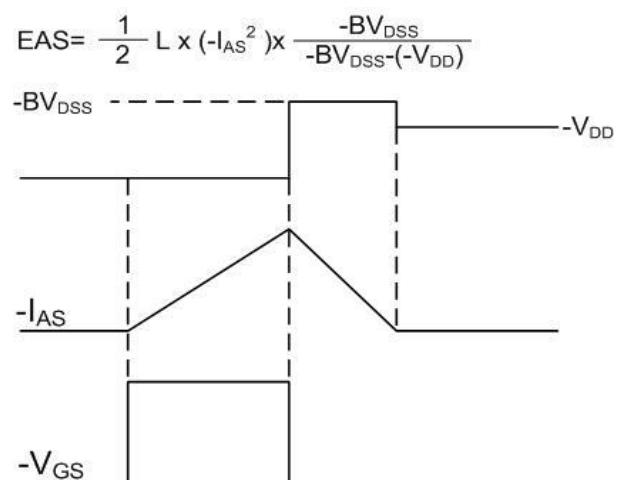
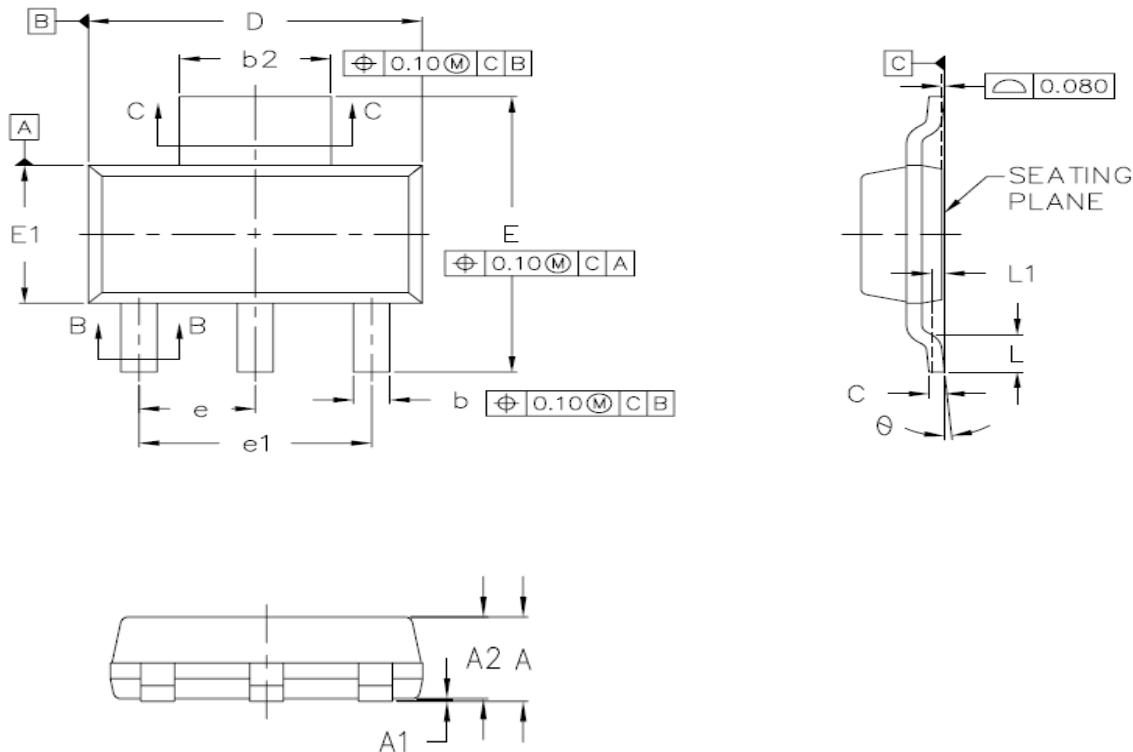


Fig.11 Unclamped Inductive Waveform

SOT-223 Package Outline



SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	—	1.80	—	0.071
A1	0.02	0.10	0.001	0.004
A2	1.50	1.70	0.059	0.067
b	0.66	0.84	0.026	0.033
b1	0.60	0.79	0.024	0.031
b2	2.90	3.10	0.114	0.122
b3	2.84	3.05	0.112	0.120
c	0.23	0.35	0.009	0.014
c1	0.23	0.33	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.30	BSC.	0.091	BSC.
e1	4.60	BSC.	0.182	BSC.
L	0.81	—	0.032	—
L1	0.25	BSC.	0.010	BSC.
θ	0°	10°	0°	10°

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